Product data sheet

1. General description

Ultrafast power diode in 2-leads TO220F plastic package.

2. Features and benefits

- Low forward voltage drop
- Low leakage current
- · Soft reverse recovery characteristics
- · High thermal cycling performance

3. Applications

- Home appliance power supply
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600				V
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 73$ °C; Fig. 1; Fig. 2; Fig. 3	10			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; $T_h \le 73$ °C; square-wave pulse	20			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.5	2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	1.6		1.6	V	
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/µs}$; $T_j = 25 \text{ °C}$; Fig. 7		- 24 35		35	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	Α	anode		K — A 001aaa020
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity		Package issue date
BYV10MX-600P	TO220F-2L	BYV10MX-600PQ	Tube	50	TO220FE-2L	21-Dec-2020

7. Marking

Table 4. Marking codes

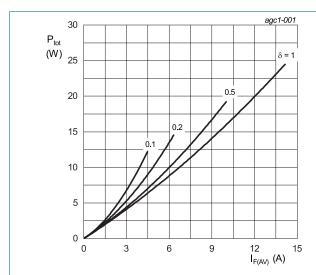
Type number	Marking codes
BYV10MX-600P	BYV10MX 600P

8. Limiting values

Table 5. Limiting values

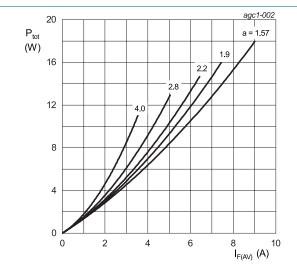
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 73$ °C; Fig. 1; Fig. 2; Fig. 3	10	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 73 °C$; square-wave pulse	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	110	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.271 \text{ V; } R_s = 0.0325 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.271 V; R_s = 0.0325 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

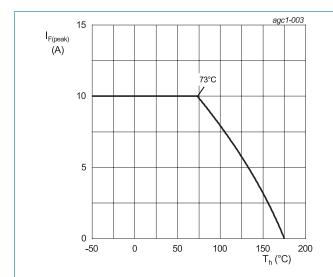


Fig. 3. Forward current as a function of heatsink temperature; maximum values

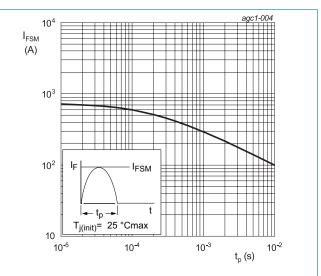
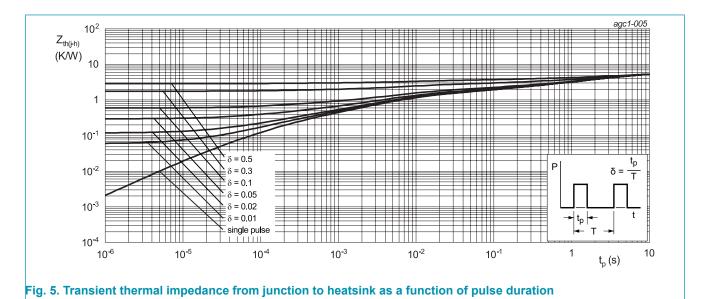


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	5.3	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

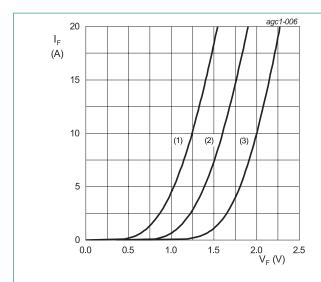
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

iaracteristics						
Parameter	Conditions		Min	Тур	Max	Unit
racteristics						
forward current	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.5	2	V
	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	-	1.6	V
reverse current	V _R = 600 V; T _j = 25 °C		-	-	8	μA
	V _R = 600 V; T _j = 150 °C		-	-	120	μA
characteristics						
reverse charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	105	-	nC
	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	282	-	nC
reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	24	35	ns
	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	45	-	ns
	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	76	-	ns
peak reverse recovery current	$I_F = 10 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_J = 25 ^{\circ}\text{C}$; Fig. 7		-	4.6	-	А
	$I_F = 10 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 125 \text{ °C}$; Fig. 7		-	7.5	-	А
	racteristics forward current reverse current characteristics reverse charge reverse recovery time	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c c} \textbf{Parameter} & \textbf{Conditions} \\ \textbf{Iracteristics} \\ \hline forward current & I_F = 10 \text{ A; } T_J = 25 \text{ °C; } \underline{\text{Fig. 6}} \\ \hline I_F = 10 \text{ A; } T_J = 150 \text{ °C; } \underline{\text{Fig. 6}} \\ \hline \text{reverse current} & V_R = 600 \text{ V; } T_J = 25 \text{ °C} \\ \hline V_R = 600 \text{ V; } T_J = 150 \text{ °C} \\ \hline \textbf{Characteristics} \\ \hline \text{reverse charge} & I_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline T_J = 25 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline I_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline T_J = 125 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline \text{reverse recovery time} & I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 100 \text{ A/µs; } \\ \hline T_J = 25 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline I_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline T_J = 25 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline T_J = 125 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline T_J = 25 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline T_J = 25 \text{ °C; } \underline{\text{Fig. 7}} \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } \\ \hline \text{legal A; } V_R = 400 \text{ V; } dI_F/dt = 200 A/µs$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{ c c c c } \hline \textbf{Parameter} & \textbf{Conditions} & \textbf{Min} & \textbf{Typ} \\ \hline \textbf{Iracteristics} \\ \hline \hline \textbf{forward current} & I_F = 10 \text{ A; } T_j = 25 \text{ °C; } \underline{\textbf{Fig. 6}} & - & 1.5 \\ \hline I_F = 10 \text{ A; } T_j = 150 \text{ °C; } \underline{\textbf{Fig. 6}} & - & - \\ \hline \textbf{reverse current} & V_R = 600 \text{ V; } T_j = 25 \text{ °C} & - & - \\ \hline \textbf{V}_R = 600 \text{ V; } T_j = 150 \text{ °C} & - & - \\ \hline \textbf{Characteristics} \\ \hline \textbf{reverse charge} & I_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 105 \\ \hline \textbf{T}_j = 25 \text{ °C; } \underline{\textbf{Fig. 7}} & - & 282 \\ \hline \textbf{reverse recovery time} & I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 24 \\ \hline \textbf{T}_j = 25 \text{ °C; } \underline{\textbf{Fig. 7}} & - & 24 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 45 \\ \hline \textbf{T}_j = 25 \text{ °C; } \underline{\textbf{Fig. 7}} & - & 45 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 76 \\ \hline \textbf{T}_j = 25 \text{ °C; } \underline{\textbf{Fig. 7}} & - & 76 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 76 \\ \hline \textbf{T}_j = 125 \text{ °C; } \underline{\textbf{Fig. 7}} & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 \text{ A; } V_R = 400 \text{ V; } dI_F/dt = 200 \text{ A/µs; } & - & 4.6 \\ \hline \textbf{I}_F = 10 $	$\begin{array}{ c c c c c } \hline \textbf{Parameter} & \textbf{Conditions} & \textbf{Min} & \textbf{Typ} & \textbf{Max} \\ \hline \textbf{Parameter} & \textbf{I}_F = 10 \ A; \ T_j = 25 \ ^{\circ}\text{C}; \ \underline{\textbf{Fig. 6}} & - & 1.5 & 2 \\ \hline \textbf{I}_F = 10 \ A; \ T_j = 150 \ ^{\circ}\text{C}; \ \underline{\textbf{Fig. 6}} & - & - & 1.6 \\ \hline \textbf{I}_F = 10 \ A; \ T_j = 150 \ ^{\circ}\text{C}; \ \underline{\textbf{Fig. 6}} & - & - & 1.6 \\ \hline \textbf{I}_F = 10 \ A; \ T_j = 25 \ ^{\circ}\text{C} & - & - & 8 \\ \hline \textbf{V}_R = 600 \ V; \ T_j = 25 \ ^{\circ}\text{C} & - & - & 120 \\ \hline \textbf{Characteristics} & & & - & - & 120 \\ \hline \textbf{Characteristics} & & & & - & 105 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 105 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 282 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 30 \ V; \ dI_F/dt = 100 \ A/\mu s; & - & 24 & 35 \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 45 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 76 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 76 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 76 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 76 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 76 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 76 & - \\ \hline \textbf{I}_F = 10 \ A; \ V_R = 400 \ V; \ dI_F/dt = 200 \ A/\mu s; & - & 7.5 & - \\ \hline \end{tabular} $



 V_o = 1.271 V; R_s = 0.0325 Ω (1) T_j = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

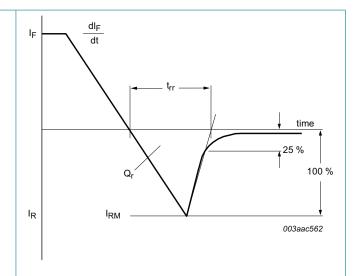
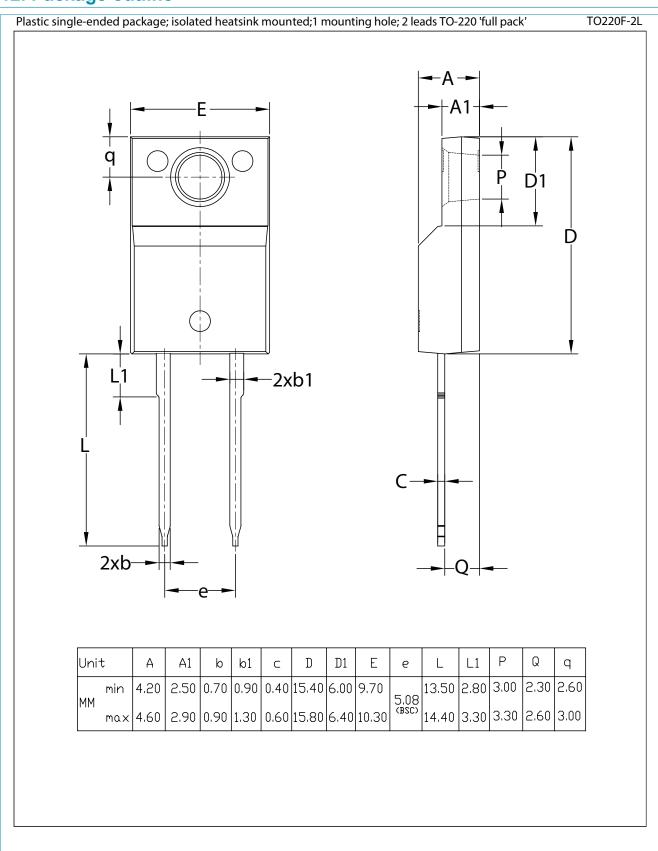


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BYV10MX-600P

Ultrafast power diode

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For more information, please visit: http://www.ween-semi.com
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